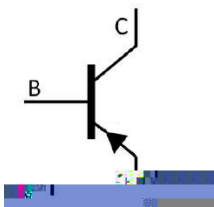


/ Descriptions

WR0<5 M M E SQS æ M ç s ll 1 Silicon PNP transistor in a TO-92 Plastic Package.

лъ 5VF4546+D, Ы ´
Complementary pair with 2SC1213(A).

æ ç æ H l ð æ æ
Low frequency power amplifier.



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

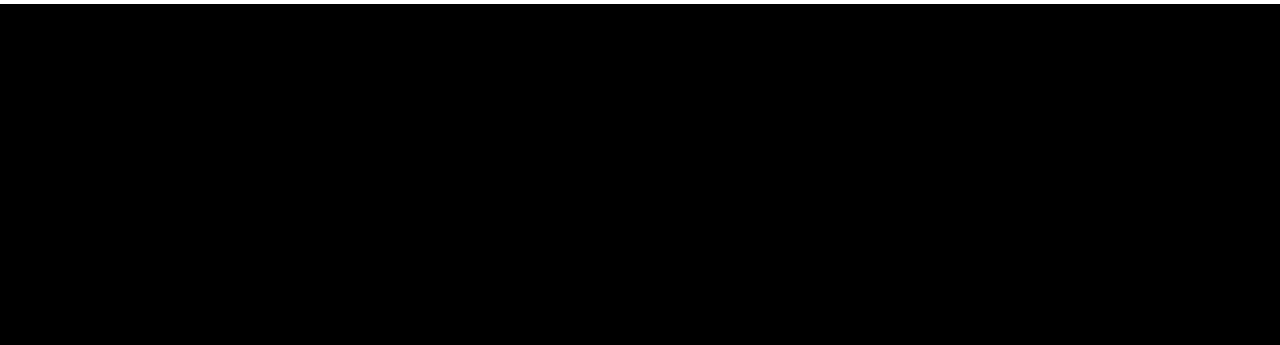
/ hFE Classifications & Marking

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	2SA673 -35	V
		2SA673A -50	
Collector to Emitter Voltage	V_{CEO}	2SA673 -35	V
		2SA673A -50	
Emitter to Base Voltage	V_{EBO}	-4.0	V
Collector Current - Continuous	I_C	-500	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

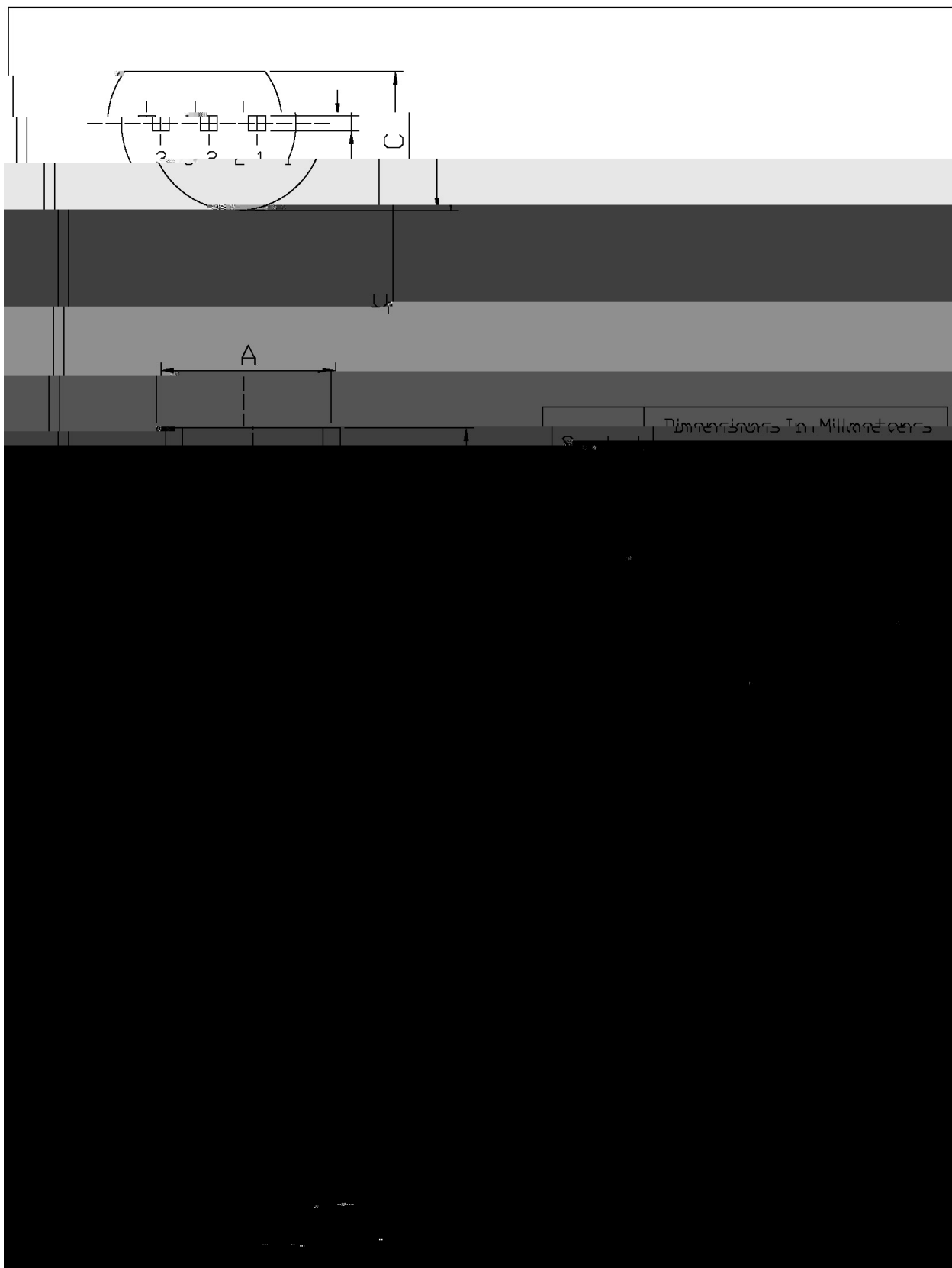
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -10\text{ A}$ $I_E = 0$	2SA673 -35			V
			2SA673A -50			
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0\text{ mA}$ $I_B = 0$	2SA673 -35			V
			2SA673A -50			
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -10\text{ A}$ $I_C = 0$	-4.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -20\text{ V}$ $I_E = 0$			-0.5	A
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -3.0\text{ V}$ $I_C = -10\text{ mA}$	60		320	
	$h_{FE(2)}$	$V_{CE} = -3.0\text{ V}$ $I_C = -500\text{ mA}$	10			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -150\text{ mA}$ $I_B = -15\text{ mA}$		-0.2	-0.6	V
Base to Emitter Voltage	V_{BE}	$V_{CE} = -3.0\text{ V}$ $I_C = -10\text{ mA}$		-0.64		V



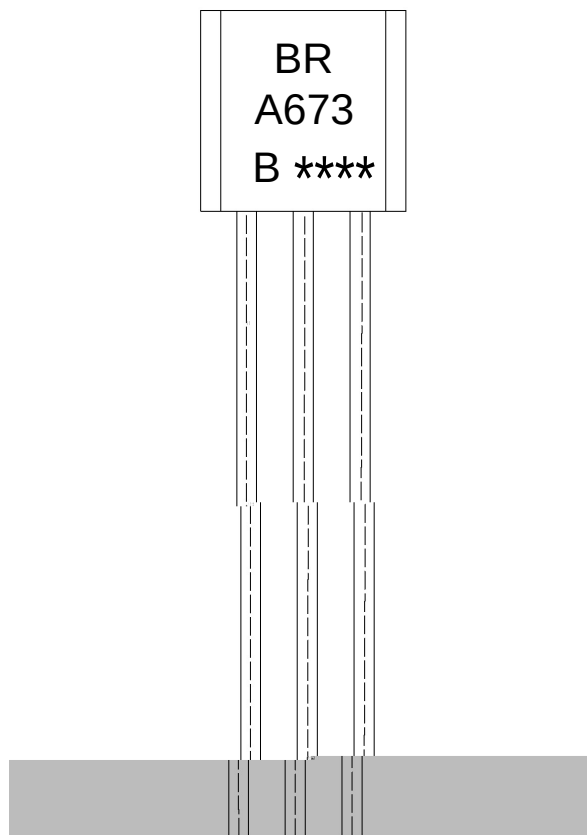
/ Package Dimensions

T O - 92

Unit: mm mm



/ Marking Instructions



б " X

EU:

№ 3^и ПД

D9: 6 X

№ 3^и ПД

E:

№ h_{FE} ' 6 ПД

---- X

№ 1 F ъ^и ПД 1 ф 1 F ъ^и ПД

Note:

BR:

Company Code.

A673:

Product Type.

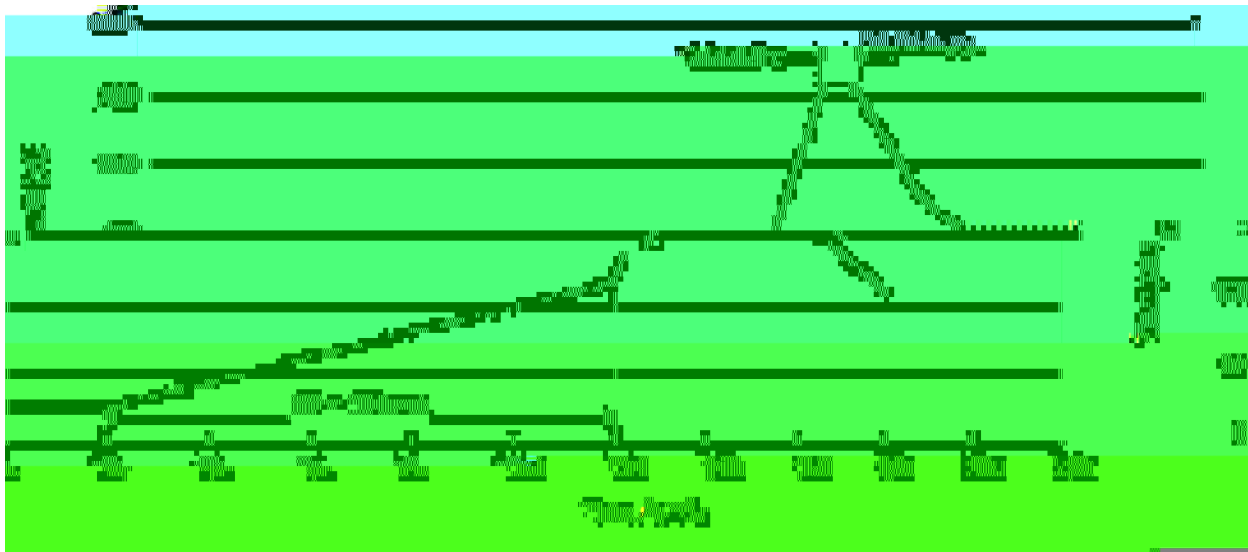
B:

h_{FE} Classifications Symbol

****:

Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



说明

1. 预加热: 25~150 °C, 时间: 60~90sec;
2. 峰值温度: 255 °C, 持续时间: 5 °C 0.5sec;
3. 冷却速度: 2~10 °C/sec.

Note:

- 1.Preheating:25~150 °C, Time:60~90sec.
- 2.Peak Temp.:255 °C, Duration:5 °C 0.5sec.
3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

温度: 270 °C ± 5 时间: 10 ± 1 sec. Temp: 270 ± 5 Time: 10 ± 1 sec

/ Packaging SPEC.

包装形式 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱